# Silicon Epitaxial Planar Schottky Barrier Diode

#### **Features**

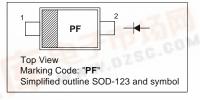
- High reliablility
- Low forward voltage

## **Application**

- For switching power supplies
- Battery protection against reversal current

#### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V <sub>RM</sub>	40	V
Reverse Voltage	V <sub>R</sub>	40	V
Average Rectified Forward Current	I <sub>F(AV)</sub>	1	А
Peak Forward Surge Current (8.3 ms)	I <sub>FSM</sub>	30	А
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	- 40 to + 150	°C

Electrical Characteristics (T<sub>a</sub> = 25 °C)

Parameter Parame	Symbol	Max.	Unit
Forward Voltage at I <sub>F</sub> = 1 A	V <sub>F</sub>	0.51	V
Reverse Current at V <sub>R</sub> = 40 V	I <sub>R</sub>	30	μΑ



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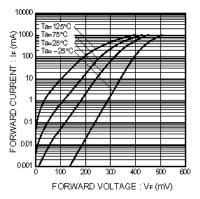


Fig. 1 Forward Temperature Characteristics

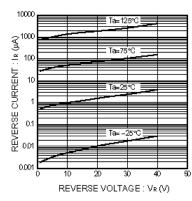


Fig.2 Reverse Temperature Characteristics

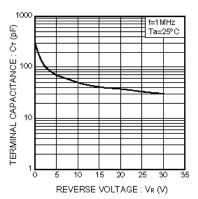
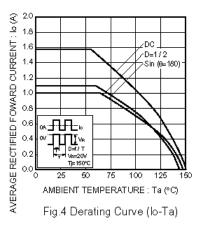
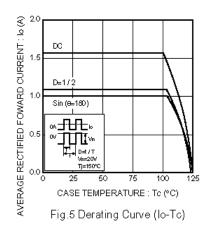


Fig.3 Capacitance Between Terminals Characteristics





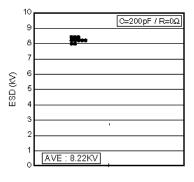


Fig.6 ESD



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### **PACKAGE OUTLINE**

Plastic surface mounted package; 2 leads

**SOD-123** 

